

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit including a fuse device, and methods for manufacturing a semiconductor integrated circuit, are disclosed. The fuse device, which is programmable by the intrusion of a flowable metal from an electrode into a junction formed in a semiconductor region, has a high initial yield and a low resistance after being programmed. The contact hole of the fuse device has a columnar insulator region having a height lower than the top end of the contact hole. The columnar insulator region limits the contact area between the electrode and the semiconductor region of the fuse device. The electrode has an excellent coverage at the upper portion of the contact hole.